
HVC132

Silicon Epitaxial Planar Pin Diode for Antenna Switching

HITACHI

ADE-208-429A (Z)
Rev. 1

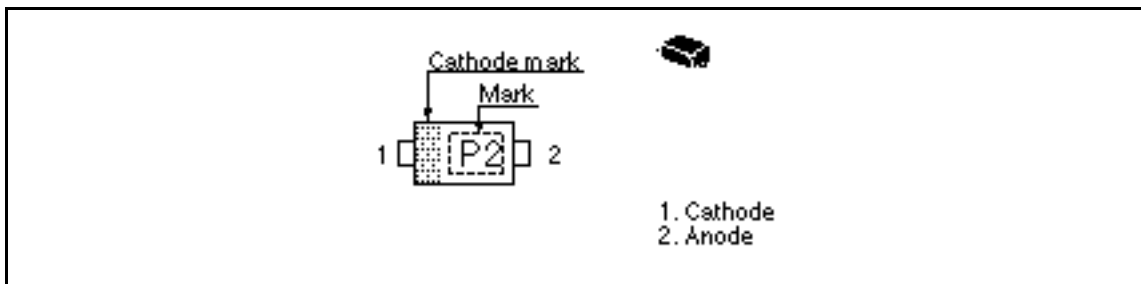
Features

- Low capacitance. ($C = 0.5\text{pFmax}$)
- Low forward resistance. ($r_f = 2.0 \text{ max}$)
- Ultra small Flat Package (UFP) is suitable for surface mount design.

Ordering Information

Type No.	Laser Mark	Package Code
HVC132	P2	UFP

Outline



HVC132

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F	100	mA
Power dissipation	Pd	150	mW
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.0	V	$I_F = 10\text{mA}$
Reverse current	I_R	—	—	0.1	μA	$V_R = 60\text{V}$
Capacitance	C	—	—	0.5	pF	$V_R = 1\text{V}$, $f = 1\text{MHz}$
Forward resistance	r_f	—	—	2.0		$I_F = 10\text{mA}$, $f = 100\text{MHz}$

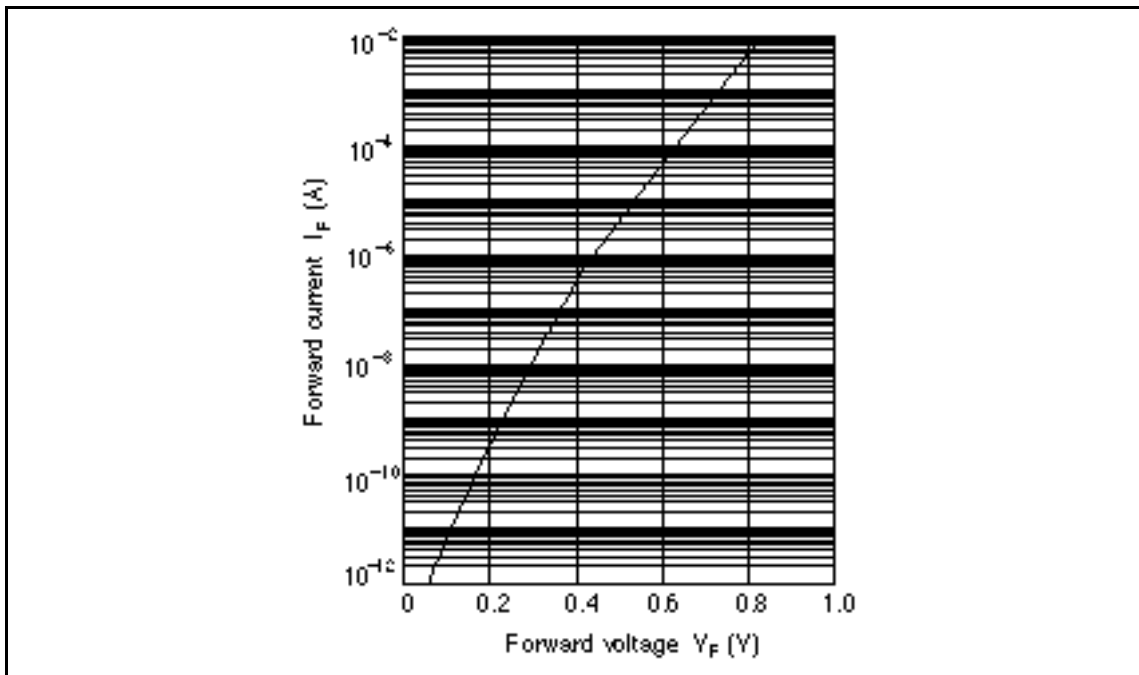


Fig.1 Forward current Vs. Forward voltage

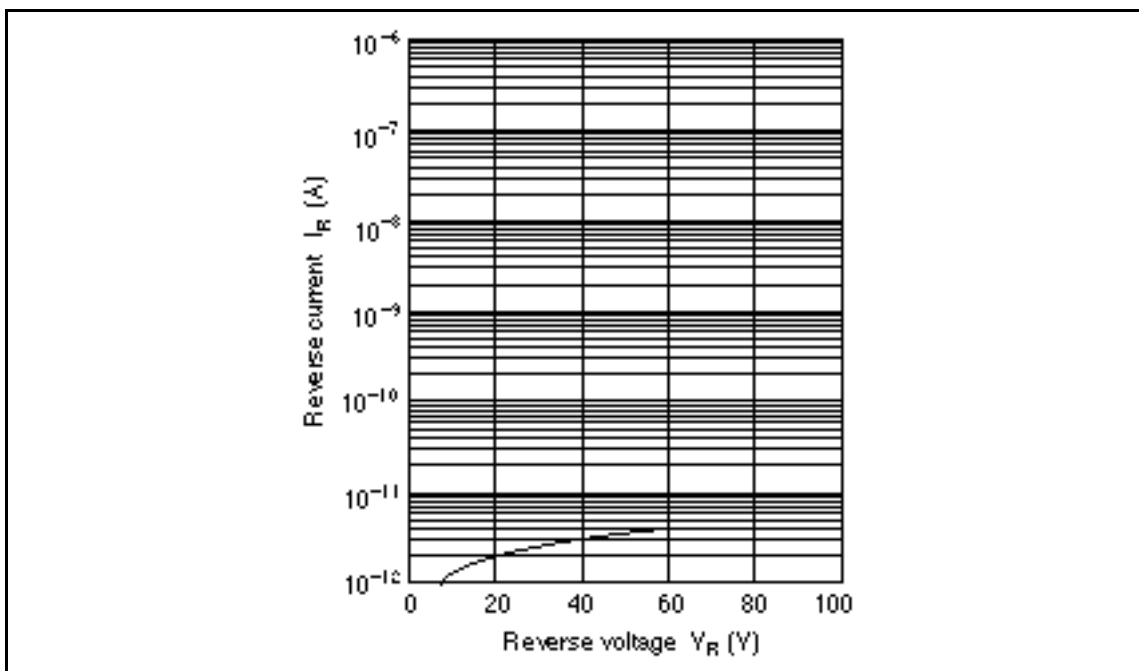


Fig.2 Reverse current Vs. Reverse voltage

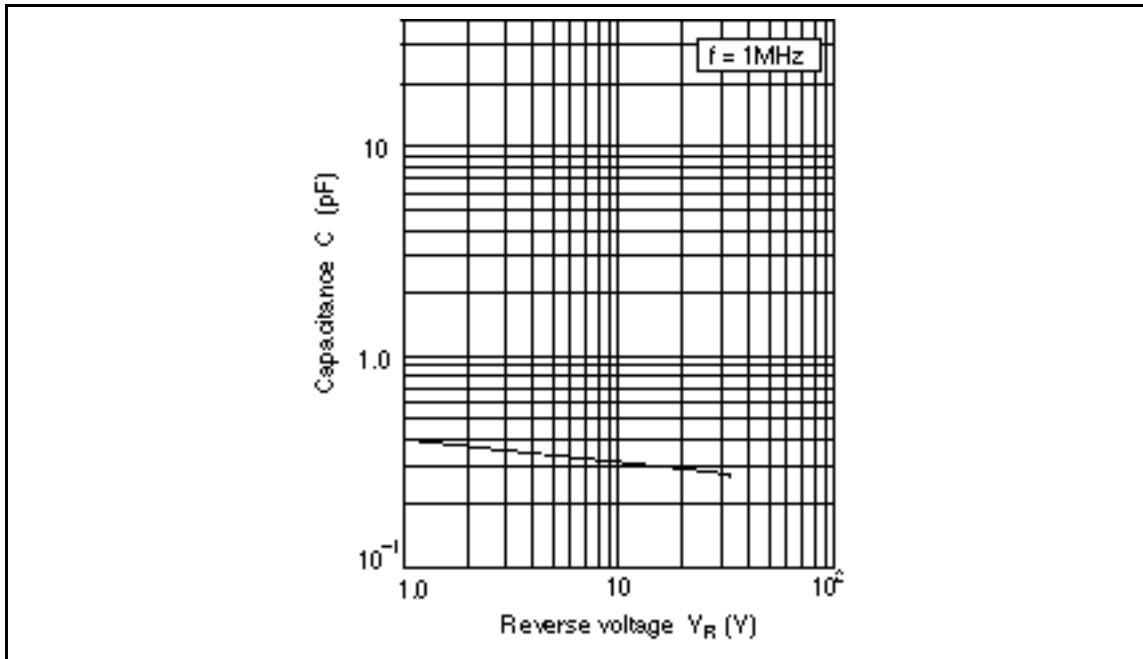


Fig.3 Capacitance Vs. Reverse voltage

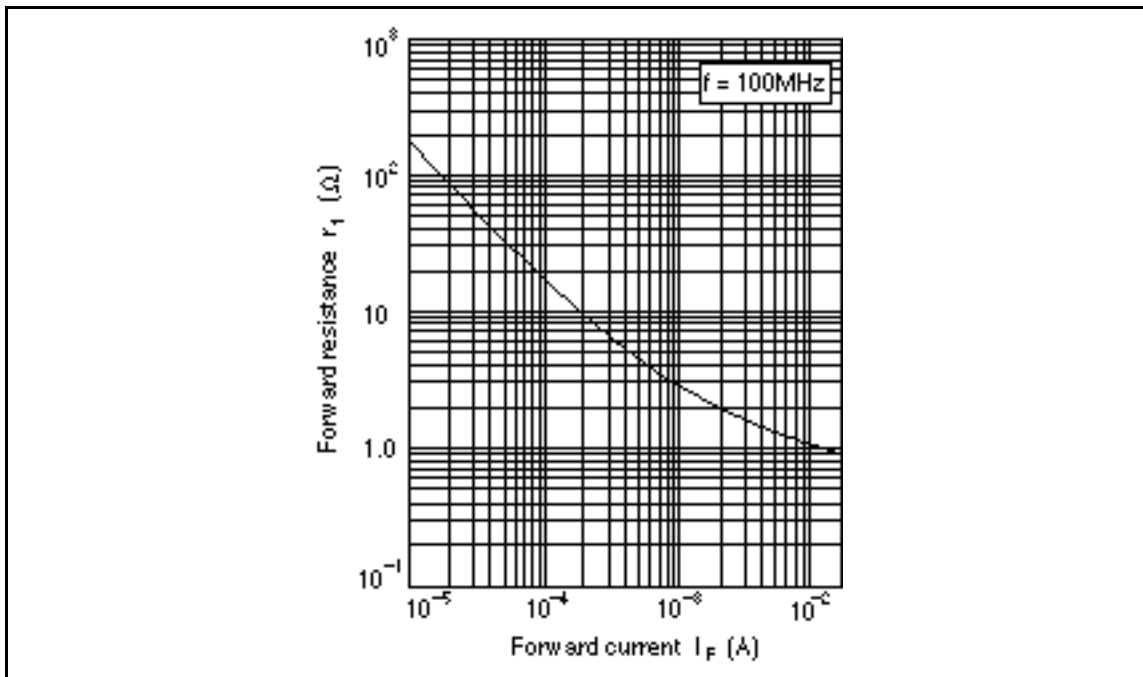


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

